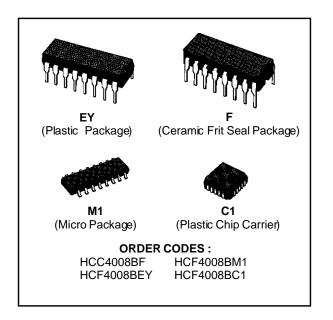


HCC/HCF4008B

4-BIT FULL ADDER WITH PARALLEL CARRY OUTPUT

- 4 SUM OUTPUTS PLUS PARALLEL LOOK-AHERD CARRY-OUTPUT
- HIGH-SPEED OPERATION-SUM IN-TO-SUM OUT 160ns (typ.) : CARRY IN-TO-CARRY OUT 50ns (typ.) AT V_{DD} = 10V, C_L = 50pF
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- 5V, 10V, AND 15V PARAMETRIC RATING
- MEETS ALL REQUIREMENTS OF JEDECTEN-TATIVE STANDARD N° 13A, "STANDARD SPE-CIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

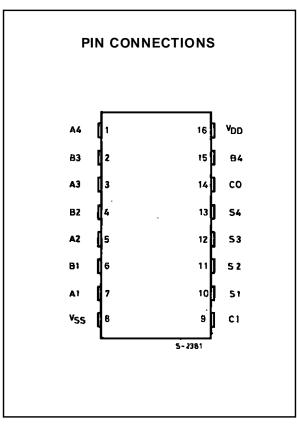


DESCRIPTION

The **HCC4008B** (extended temperature range) and **HCF4008B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4008B** types consist of four full adder stages with fast look ahead carry provision from stage to stage. Circuitry is included to provide a fast "parallel-carry-out" to permit high-speed operation in arithmetic sections using several HCC/HCF 4008B's.

HCC/HCF4008B inputs include the four sets of bits to be added, A_1 to A_4 and B_1 to B_4 , in addition to the "Carry In" bit from a previous section. **HCC/HCF4008B** outputs include the four sum bits, S_1 to S_4 . In addition to the high speed "parallel-carryout" which may be utilized at a succeeding **HCC/HCF4008B** section.



June 1989 1/13

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
Vi	Input Voltage	- 0.5 to V _{DD} + 0.5	V
II	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200 100	mW mW
Тор	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	∞
T _{stg}	Storage Temperature	- 65 to + 150	°C

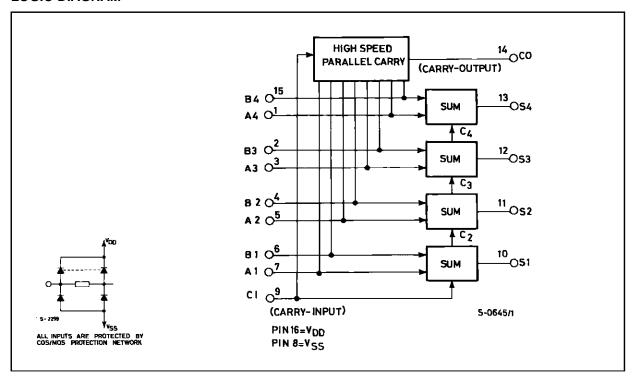
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
VI	Input Voltage	0 to V _{DD}	V
Top	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	ڻ ڻ

LOGIC DIAGRAM



TRUTH TABLE

Ai	Bi	CI	СО	SUM
0	0	0	0	0
1	0	0	0	I
0	I	0	0	I
1	I	0	I	0
0	0	I	0	I
1	0	I	I	0
0	I	l I	I	0
1	I	I	I	I

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

			Т	est Con	dition	s	Value							
Symbol	Parame	ter	٧ı	٧o	$ I_0 $	V _{DD}	ΤL	* o w		25°C		Тн	igh *	Unit
			(V)	(V)	(μA)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
ΙL	Quiescent		0/ 5			5		5		0.04	5		150	
	Current	HCC	0/10			10		10		0.04	10		300	
		Types	0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	μΑ
		ПОЕ	0/ 5			5		20		0.04	20		150	
		HCF Types	0/10			10		40		0.04	40		300	
		7,7	0/15			15		80		0.04	80		600	
V _{OH}	Output Hig	h	0/ 5		< 1	5	4.95		4.95			4.95		
	Voltage		0/10		< 1	10	9.95		9.95			9.95		V
			0/15		< 1	15	14.95		14.95			14.95		
V _{OL}	Output Low	1	5/0		< 1	5		0.05			0.05		0.05	
	Voltage		10/0		< 1	10		0.05			0.05		0.05	V
			15/0		< 1	15		0.05			0.05		0.05	
V _{IH}	Input High			0.5/4.5	< 1	5	3.5		3.5			3.5		
	Voltage			1/9	< 1	10	7		7			7		V
				1.5/13.5	< 1	15	11		11			11		
V_{IL}	V _{IL} Input Low			4.5/0.5	< 1	5		1.5			1.5		1.5	
	Voltage			9/1	< 1	10		3			3		3	V
				13.5/1.5	< 1	15		4			4		4	
I _{OH}	Output Drive		0/ 5	2.5		5	- 2		- 1.6			<u> </u>	-	
	Current	HCC	0/ 5	4.6		5	- 0.64		- 0.51			- 0.36		
		Types	0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		mA
			0/ 5	2.5		5	- 1.53		 	- 3.2		- 1.1		
		HCF	0/ 5	4.6		5	- 0.52		- 0.44			- 0.36		
		Types	0/10	9.5		10	- 1.3		- 1.1			- 0.9		
	0		0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4		
I _{OL}	Output Sink	нсс	0/ 5	0.4		5	0.64		0.51	1		0.36		
	Current	Types	0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		mA
		HCF	0/ 5	0.4		5	0.52		0.44	1		0.36		
		Types	0/10	0.5		10	1.3		1.1	2.6		0.9		
	lanut	1100	0/15	1.5		15	3.6	101	3.0	6.8 ±10 ⁻⁵	101	2.4	4	
I _{IH} , I _{IL}	Input Leakage	HCC Types	0/18			18		± 0.1		±10 °	± 0.1		± 1	_
	Current HCF	HCF Types	0/15	Any In	put	15		± 0.3		±10 ⁻⁵	± 0.3		± 1	μΑ
Cı	Input Capa			Any In	put					5	7.5			pF
* T	par Gapa	21101100	40°C			<u> </u>	<u> </u>	<u> </u>	L		L	<u> </u>	l	יץ

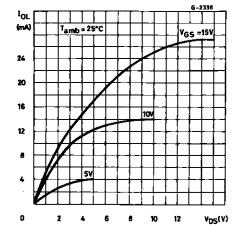
^{*} T_{Low} = - 55°C for **HCC** device : - 40°C for **HCF** device. * T_{High} = + 125°C for **HCC** device : + 85°C for **HCF** device. The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.



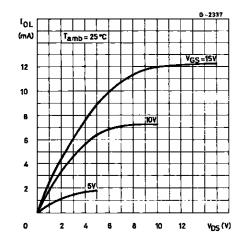
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25 °C, C_L = 50 pF, R_L = 200 k Ω , typical temperature coefficient for all V_{DD} values is 0.3 %/°C, all input rise and fall times = 20 ns)

Symbol	Darama	40.0	er Test Conditions			Value		11:4
Symbol	Parame	eter		V _{DD} (V)	Min.	Тур.	Max.	Unit
t _{PLH} , t _{PHL}	Propagation Delay	Delay Sum In to	5		400	800		
	Time	Sum Out		10		160	320	
				15		115	230	
		Carry In to		5		370	740	
		Sum Out		10		155	310	
			15		115	230	ns	
		Sum In to Carry Out		5		200	400	115
				10		90	180	
				15		65	130	
		Carry In to	Carry In to	5		100	200	
		Carry Out		10		50	100	
				15		40	80	
t _{THL} , t _{TLH}	Transition Time			5		100	200	
				10		50	100	ns
				15		40	80	

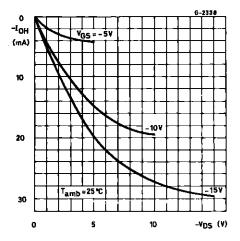
Typical Output Low (sink) Current.



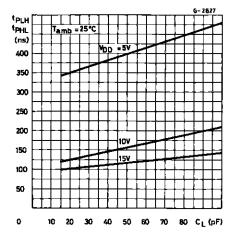
Minimum Output Low (sink) Current Characteristics.



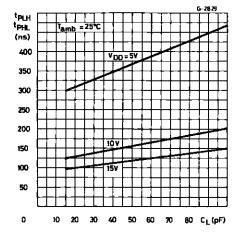
Typical Output High (source) Current Characteristics.



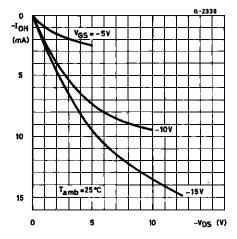
Typical Sum-in to Sum Out Propagation Delay vs. Load Capacitance.



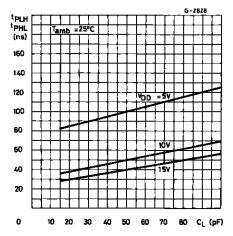
Typical Carry-in to Sum Out Propagation Delay Time vs. Load Capacitance.



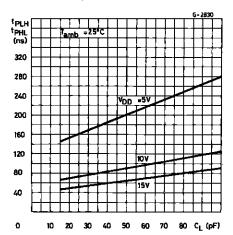
Minimum Output High (source) Current Characteristics.



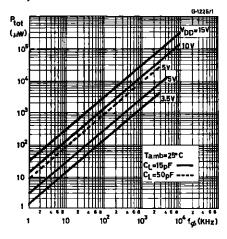
Typical Carry-in to Carry-Out Propagation Delay vs. Load Capacitance.



Typical Sum-in to Carry-Out Propagation Delay Time vs. Load Capacitance.

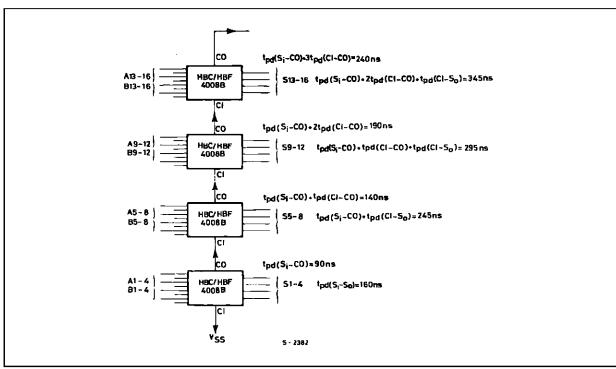


Typical Dynamic Power Dissipation/Package vs. Frequency.



TYPICAL APPLICATIONS

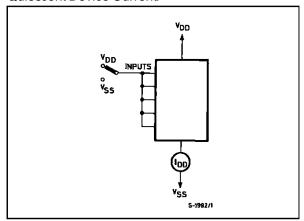
SPEED CHARACTERISTICS OF A 16-BIT ADDER.



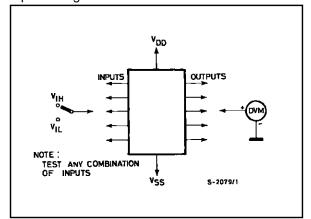
Notes :All "A" and "B" input bits occur at t=0. All sums settled at t=345ns $C_L=50$ pF, $T_{amb}=25$ °C, V_{DD} - $V_{SS}=10$ V.

TEST CIRCUITS

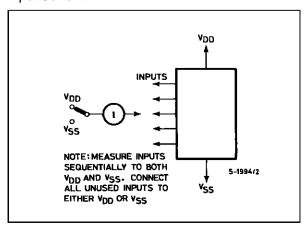
Quiescent Device Current.



Input Voltage.



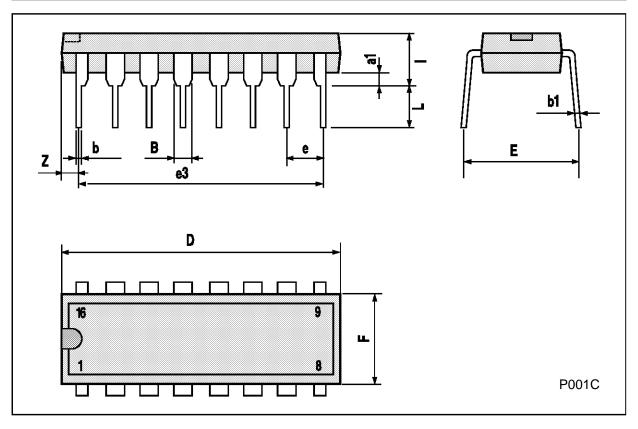
Input Current.





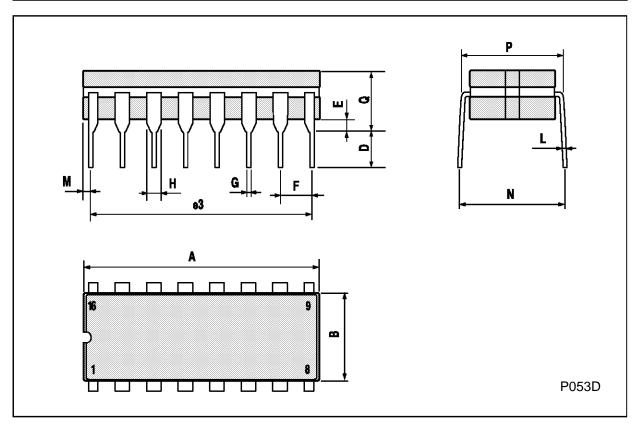
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm		inch				
5	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
ı			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



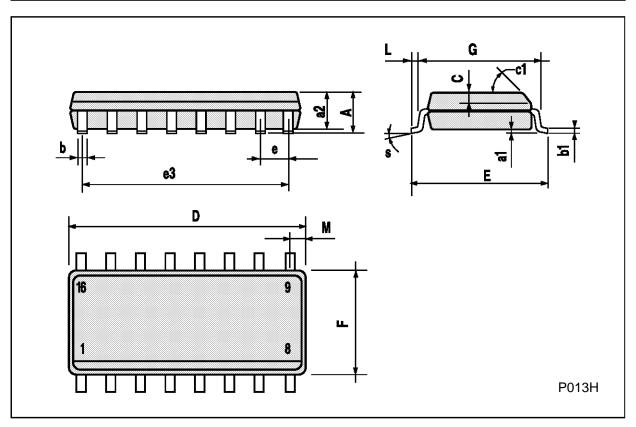
Ceramic DIP16/1 MECHANICAL DATA

DIM.		mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			20			0.787	
В			7			0.276	
D		3.3			0.130		
E	0.38			0.015			
e3		17.78			0.700		
F	2.29		2.79	0.090		0.110	
G	0.4		0.55	0.016		0.022	
Н	1.17		1.52	0.046		0.060	
L	0.22		0.31	0.009		0.012	
М	0.51		1.27	0.020		0.050	
N			10.3			0.406	
Р	7.8		8.05	0.307		0.317	
Q			5.08			0.200	



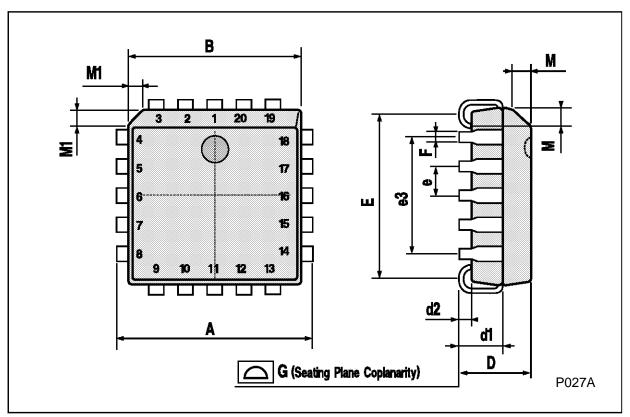
SO16 (Narrow) MECHANICAL DATA

DIM.		mm		inch					
Diivi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.			
Α			1.75			0.068			
a1	0.1		0.2	0.004		0.007			
a2			1.65			0.064			
b	0.35		0.46	0.013		0.018			
b1	0.19		0.25	0.007		0.010			
С		0.5			0.019				
c1			45°	(typ.)					
D	9.8		10	0.385		0.393			
Е	5.8		6.2	0.228		0.244			
е		1.27			0.050				
e3		8.89			0.350				
F	3.8		4.0	0.149		0.157			
G	4.6		5.3	0.181		0.208			
L	0.5		1.27	0.019		0.050			
М			0.62			0.024			
S		8° (max.)							



PLCC20 MECHANICAL DATA

DIM.		mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		



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